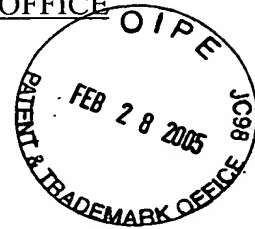


JFW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE
ATTY. DOCKET NO.



In re Patent Application of Steven E. Hill

Serial No. 10/761,408

Group Art Unit: 2828

Filed: January 22, 2004

Examiner:

For: LIGHT EMITTING DIODES AND PLANAR OPTICAL LASERS
USING IV SEMICONDUCTOR NANOCRYSTALS

INFORMATION DISCLOSURE STATEMENT

This Information Disclosure Statement is being filed in the manner prescribed by 37 CFR 1.97(b) - (d) to satisfy the duty under 37 CFR 1.56 to disclose to the Office information, known to individuals associated with the filing and prosecution of the subject application, which is material to the examination of the application.

In accordance with 37 CFR 1.97(g) and (h), this statement is not to be construed as a representation that a search has been made or an admission that the information cited herein is, or is considered to be, material to patentability as defined in 37 CFR 1.56(b).

This Information Disclosure Statement is being filed within three months of the filing date of a national application; within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; or before the mailing date of a first official action on the merits and therefore applicant respectfully requests consideration under 37 CFR 1.97(b).

In compliance with 37 CFR 1.98(a)(2), also enclosed is a legible copy of:

- i) each foreign patent; and

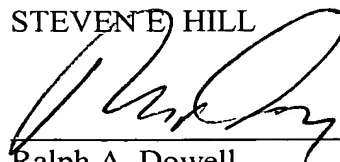
In compliance with 37 CFR 1.98(a)(1), a list of all patents, publications, applications or other information submitted for consideration by the Office is hereby provided by way of the attached Form PTO-1449.

It is respectfully requested that the information be expressly considered by the Examiner and that the references be made of record and appear among the "References Cited" on any patent to issue therefrom.

The Patent Office is hereby authorized to charge any deficiency, or credit any overpayment in fees to Deposit Account Number 19-2550.

Respectfully submitted,

STEVEN E HILL



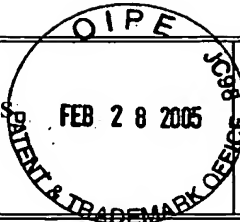
Ralph A. Dowell
Reg. No. 26,868

Dated: 2/24/2005

RAB:bbp

Encls.: Form PTO-1449
 A copy of each reference
 (excluding copies of US patent references)

Form PTO-1449 (Modified) LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	Atty. Docket No. 50422-6 Applicant Steven E. Hill Filing Date January 22, 2004	Serial No. 10/761,408 Group 2828
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REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FIL. DATE IF APPROPRIATE
AA	5,667,905	1997.09.16	Campisano, Salvatore Ugo et al.			
AB	6,255,669	2001.07.03	Birkhahn, Ronald H. et al.			
AC	US 2003/034486	2003.02.20	Korgel, Brian A.			
AD	US 2002/048289	2002.04.25	Atanackovic, Petar B et al.			
AE	US 2004/183087	2004.09.23	Gardner, Donald S.			
AF	5,422,907	1995.06.06	Bhargava, Raneshwar N.			
AG	5,637,258	1997.06.10	Goldburt, Efim T. et al.			

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
					YES	NO
AH	101 04 193	2002.08.01	DE			
AI	2001 203382	2001.07.27	JP			
AJ	1 134 799	2001.09.19	EP			
AK	WO 02/061815	2002.08.08	DE			
AL	0 650 200	1995.04.26	EP			

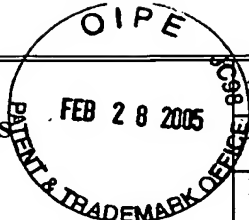
OTHER ART (including Author, Title, Date, Pertinent Pages, Etc.)

AM	Orlov, L.K. et al.	COMPARITIVE ANALYSIS OF LIGHT EMMITTING PROPERTIES OF Si:Er AND Ge/Si _{1-x} Ge _x EPITAXIAL STRUCTURES OBTAINED BY MBE METHOD. <i>Gettering and Defect Engineering in Semiconductor Technology, Solid State Phenomena (FORMERLY Part B of "Diffusion and Defect Data [0377-6883])</i> . Vol 69 until 70, 1999. Pages 377-382. ISSN:1012-0394.
AN	Shin, J.H. et al.	CONTROLLING THE QUANTUM EFFECTS AND ERBIUM-CARRIER INTERACTION USING Si/SiO ₂ SUPERLATTICES. <i>Proceedings of the SPIE</i> . Vol. 4282, January 1, 2001. Bellingham, VA United States of America. Pages 142-152.
AO	Yun, F. et al.	ROOM TEMPERATURE SINGLE-ELECTRON NARROW-CHANNEL MEMORY WITH SILICONNANODOTS EMBEDDED IN SiO ₂ MATRIX. <i>Japanese Journal of Applied Physics</i> . Publication Office Japanese Journal of Applied Physics. Vol. 39, no. 8A Part II. August 1, 2000. Tokyo, Japan. Pages L792- L795.

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449 (Modified) LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	Atty. Docket No. 50422-6 Applicant Steven E. Hill	Serial No. 10/761,408 Filing Date January 22, 2004 Group 2828
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REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FIL. DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

EXAM. INIT.	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
						YES	NO

OTHER ART (including Author, Title, Date, Pertinent Pages, Etc.)

AP	Rozo, C. et al.	SPECTOSCOPIC STUDY OF RARE EARTH DOPED NANO-CRYSTALLINE SILICON IN SiO ₂ FILMS. <i>Quantum Confined Semiconductor Nanostructures. Symposium (Mater. Res. Soc. Symposium Proceedings Vol. 737) Mater Res. Soc Warrendale, Pa, USA, 2003. Pages 517-522, XP 002310621. ISBN:1-55899-674-5</i>
AQ	Fujii, Minoru et al.	EXCITATION OF INTRA-4f SHELL LUMINESCENCE OF Yb ³⁺ BY ENERGY TRANSFER FROM Si NANOCRYSTALS. <i>Applied Physics Letters. American Institute of Physics. New York, USA. Vol. 73, no. 21. 23 November 1998, Pages 3108-3110, XP 012021485. ISSN: 0003-6951.</i>
AR	Pacifici, D. et al.	ERBIUM-DOPED Si NANOCRYSTALS: OPTICAL PROPERTIES AND ELECTROLUMINESCENT DEVICES. <i>Physica E. Elsevier netherlands, Vol. 16, no. 3-4, March 2003. Pages 331-340, XP 002310622. ISSN: 1386-9477.</i>
EXAMINER		DATE CONSIDERED

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